

Silicon PNP Power Transistors

2SA671

DESCRIPTION

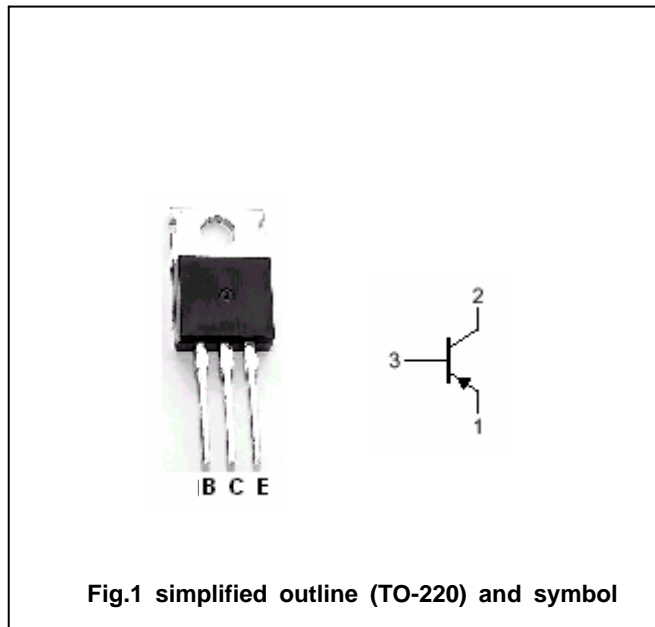
- With TO-220 package
- Complement to type 2SC1061
- Low collector saturation voltage
- Note: type 2SA670 with short pin

APPLICATIONS

- Designed for use in low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-50	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-4	V
I _C	Collector current		-3	A
I _{CM}	Collector current-peak		-6	A
I _B	Base current		-0.5	A
P _C	Collector power dissipation	T _C =25	25	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	5.0	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA, I _B =0	-50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-5mA, I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-2A; I _B =-0.2A			-1.0	V
V _{BE}	Base-emitter on voltage	I _C =-1A; V _{CE} =-4V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-25V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-4V; I _C =0			-100	μA
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-4V	35		320	
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-4V	35			
f _T	Transition frequency	I _C =-0.5A; V _{CE} =-4V	5.0			MHz

◆ h_{FE-1} Classifications

A	B	C	D
35-70	60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)